

DMSMS NOTICE

DIMINISHING MANUFACTURING SOURCES AND MATERIAL SHORTAGES


1. TITLE CAES PRODUCT DISCONTINUANCE NOTIFICATION FOR THE MICROCIRCUIT, MEMORY, DIGITAL, CMOS, 512K x 8-BIT, RADIATION-HARDENED LOW VOLTAGE SRAM, MONOLITHIC SILICON		2. DOCUMENT NUMBER SPO-2019-D-0011	
		3. DATE (Year, Month, Date) 2019, 10, 12	
4. MANUFACTURER NAME AND ADDRESS CAES 4350 CENTENNIAL BOULEVARD COLORADO SPRINGS, COLORADO 80907-3701		5. MANUFACTURER POINT OF CONTACT (NAME) Peter Nelson	
		6. MANUFACTURER POINT OF CONTACT TELEPHONE 719-594-8238	
		7. MANUFACTURER POINT OF CONTACT EMAIL peter.b.nelson@cobhamaes.com	
8. CAGE CODE 65342	9. MANUFACTURER FINAL ORDER DATE 30 September 2020	10. PRODUCT IDENTIFICATION CODE WJ02	11. BASE PART UT8Q512E
12. BLANK		13. SMD NUMBER 5962-99607	14. DEVICE TYPE DESIGNATOR 05, 06
		15. RHA LEVELS All	16. QML LEVEL Q, V
		17. NON QML LEVEL N/A	18. GIDEP NUMBER GB4-D-20-0003
19. COMMENTS CAES is issuing this diminishing manufacturing sources and material shortages notice to announce the end of life (EOL) for SMD number 99607, device types 05 and 06. CAES will accept orders on the remaining inventory on a first-come, first-served basis through September 30, 2020 or until existing inventory is depleted, whichever comes first. Additionally, all die sales will not longer be available. A new version will be available under device type 07. This new device type has improved ESD and TID performance, increased to 4kV and 100 krad(Si) respectively. Electrically, the standby current at room and cold temperatures has increased from 9mA to 16mA. VOH1 and VOH2 have been changed from 2.4V and $V_{DD}-0.1$ to 2.2V and $0.8 \cdot V_{DD}$, respectively. Additionally, Input Capacitance (Cin) and Bi-directional I/O capacitance has increased from 10 and 12 pF to 14 and 16 pF respectively.			
20. ADEPT REPRESENTATIVE Tim Meade		21. SIGNATURE 	
		22. DATE 10/12/19	

Table 1

Standard PN	Source	Vendor PN	Description
5962L9960705Q9B	CAES	UT8Q512E_QDIE	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960705QYA	CAES	UT8Q512E-YCA	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960705QYC	CAES	UT8Q512E-YCC	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960705V9B	CAES	UT8Q512E_VDIE	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960705VYA	CAES	UT8Q512E-VCA	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960705VYC	CAES	UT8Q512E-VCC	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960706Q9B	CAES	UT8Q512E_QDIE	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960706QYA	CAES	UT8Q512E-YWA	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960706QYC	CAES	UT8Q512E-YWC	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960706V9B	CAES	UT8Q512E_VDIE	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960706VYA	CAES	UT8Q512E-VWA	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS
5962L9960706VYC	CAES	UT8Q512E-VWC	MEMORY, RAD HARD, SRAM, 512K X 8-BIT, LOW VOLTAGE, 20 NS